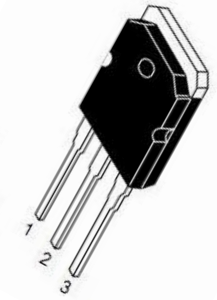
NPN/PNP ComplementarySilicon Power Transistors

◆ Features：

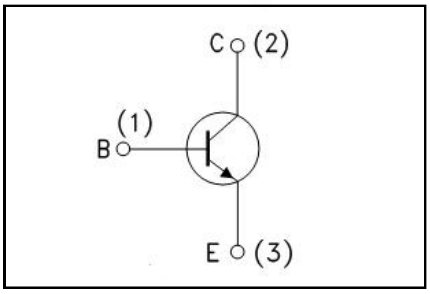
- ✧ High efficiency,low deviation
  高效率，低偏差
- ✧ Small input impedance,low consumption of power
  输入阻抗小，功耗低
- ✧ Resistant of high temperature,high humidity
  抗高温、高湿
- ✧ Good stability,reliability
  稳定性好，可靠性高

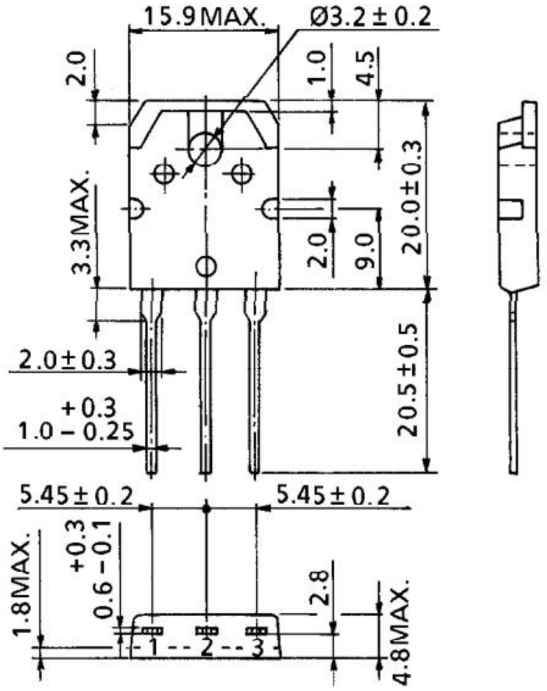
TO-3PNT



◆ Applications

- ✧ Audio amplifier
  音频放大器
- ✧ Switching applications
  开关应用
- ✧ Complement to Type TIP36C(PNP)
  与 TIP36C(PNP)互补应用
- ✧ Recommend for 125W high fidelity audio frequency amplifier output stage applications
  推荐用于 125W 高保真音频放大器输出级应用





◆ **Absolute Maximum Ratings** (Tc=25°C)

Symbol	**Parameters**	**Ratings**	Unit
VCBO	Collector-Base Voltage 集电极 - 基极电压	**150**	V
VCEO	Collector-Emitter Voltage 集电极 - 发射极电压	**120**	V
VEBO	Emitter-Base Voltage 发射极 - 基极电压	**7**	V
I_C	Collector Current-Continuous 集电极连续电流	**11**	A
I_B	Base Current-Continuous 基极连续电流	**1**	A
PC	Collector Power Dissipation 耗散功率	**125**	W
T_j	Max.Operating junction temperature 最大结温	**150**	℃
Tstg	Storage Temperature 存储温度	**-65 ~ +150**	℃

◆ Electrical characteristics (Tc=25°C unless otherwise noted)

Symbol	Parameters	Min	Typ	Max	Units	Conditions
I_{CBO}	Collector Cutoff Current 集电极截止电流	**--**	**--**	**1.0**	µA	V_{CE}=220V，I_B=0
I_{EBO}	Emitter Cutoff Current 发射极截止电流	**--**	**--**	**1.0**	µA	V_{EB}=10V，I_C=0
BV_{CEO}	Collector Emitter Sustaining voltage(Note 1) 集电极发射极持续电压	**120**	**--**	**--**	V	I_C=50mA，I_B=0
VCE(sat)	Collector Emitter Saturation Voltage(Note 1) 集电极发射极饱和电压	**--**	**--**	**1.5**	V	I_C=8A,I_B=0.8A
h_{FE}	DC Current Gain(Note 1) 直流电流增益	**80**	**--**	**160**		I_C=1A，V_{CE}=5V
f_T	Current-Gain—Bandwidth 电流增益带宽	**10**	**--**	**--**	MHz	VCE=5V， Ic=1A，f=1MHz

Note 1: Pulse test: PW <= 300us , duty cycle <= 2%.